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November 2013

### FQPF9N50C

## N-Channel QFET® MOSFET

500 V, 9 A, 800 mΩ

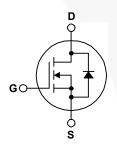
### **Description**

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize onstate resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

#### **Features**

- 9 A, 500 V,  $R_{DS(on)}$  = 800 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 4.5 A
- Low Gate Charge (Typ. 28 nC)
- Low Crss (Typ. 24 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF9N50C	Units	
$V_{DSS}$	Drain-Source Voltage		500	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	C)	9 *	А	
	- Continuous (T <sub>C</sub> = 100°C)		5.4 *	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	36 *	Α	
$V_{GSS}$	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	360	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	9	A	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	13.5	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		44	W	
	- Derate above 25°C		0.35	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

<sup>\*</sup> Drain current limited by maximum junction temperature.

#### **Thermal Characteristics**

Symbol	Parameter	FQPF9N50C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.86	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF9N50C	FQPF9N50C	TO-220F	Tube	N/A	N/A	50 units

### **Electrical Characteristics** T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	500			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		0.57		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V			1	μΑ
		V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V		-	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		0.65	0.8	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_D = 4.5 \text{ A}$	\\ <b></b>	6.5		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		790	1030	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		130	170	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			24	30	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 9 A,		18	45	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 250 \text{ V}, I_D = 9 \text{ A},$ $R_G = 25 \Omega$		65	140	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	11.6 - 20 32		93	195	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		64	125	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 9 A,		28	35	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		4		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	/	15		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				9	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				36	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 9 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 9 A,		335		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		2.95	//	μС

- Notes: Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 8 mH,  $I_{AS}$  = 9 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 3.  $I_{SD}$  ≤ 9 A, di/dt ≤ 200 A/µs,  $V_{DD}$  ≤ BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

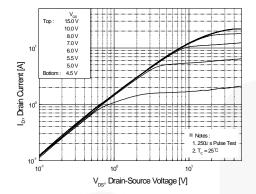


Figure 1. On-Region Characteristics

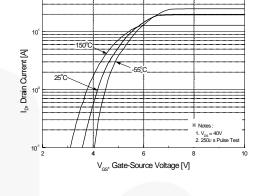


Figure 2. Transfer Characteristics

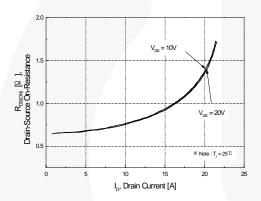


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

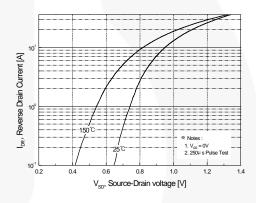


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

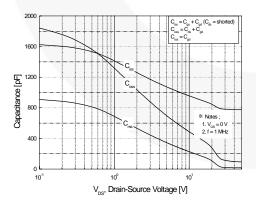


Figure 5. Capacitance Characteristics

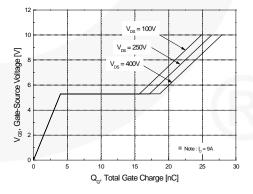


Figure 6. Gate Charge Characteristics

### Typical Characteristics (continued)

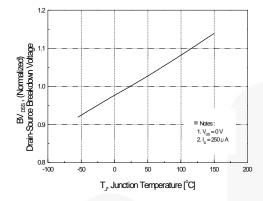


Figure 7. Breakdown Voltage Variation vs Temperature

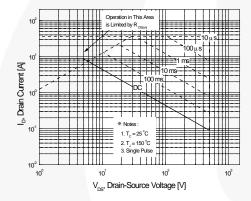


Figure 9. Maximum Safe Operating Area

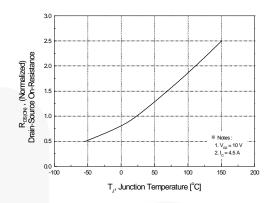


Figure 8. On-Resistance Variation vs Temperature

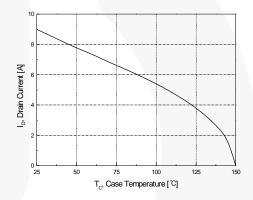


Figure 10. Maximum Drain Current vs Case Temperature

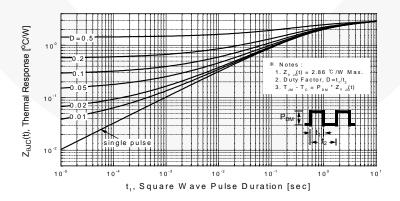


Figure 11. Transient Thermal Response Curve

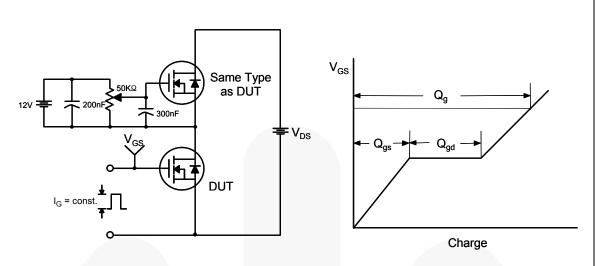


Figure 12. Gate Charge Test Circuit & Waveform

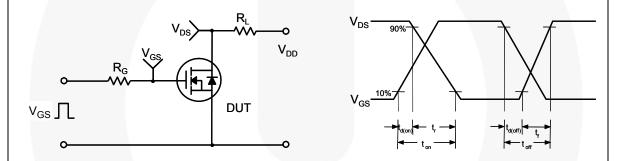


Figure 13. Resistive Switching Test Circuit & Waveforms

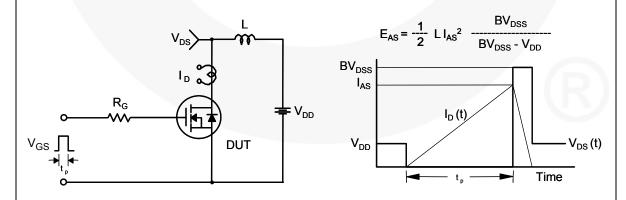
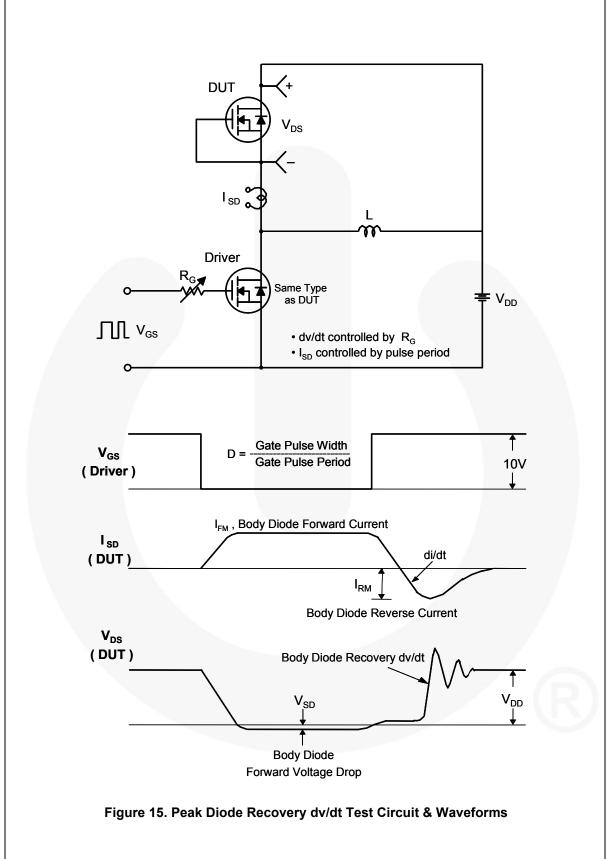


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



#### **Mechanical Dimensions**

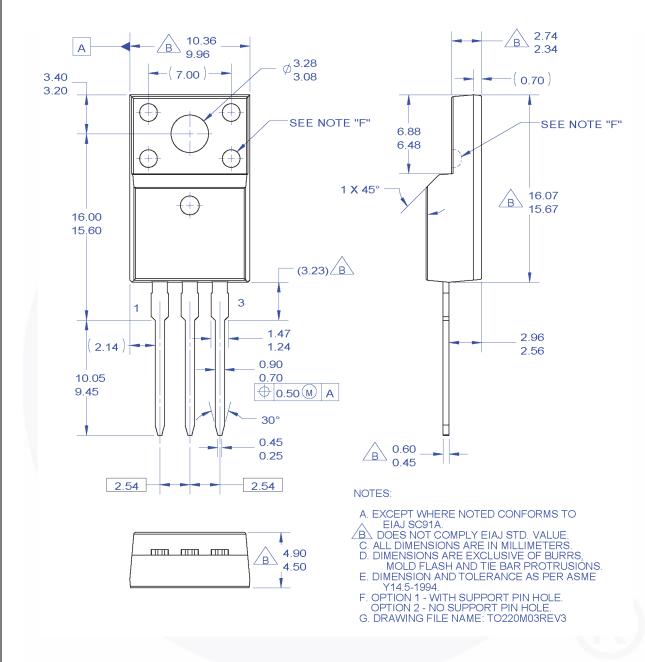


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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